MODIFIED PTO/SB/08 A & B (06-03)

Substitute for Form 1449 A & B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 1

Complete if Known	
Application Number	10/540,514
Confirmation Number	Unassigned
Filing Date	June 23, 2005
First Named Inventor	Takenori OSADA
Art Unit	Unassigned
Examiner Name	Unassigned
Attorney Docket Number	Q88664

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number: Number	Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		US			
		US			
		US			
		US			
		US			

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document: Country Code[3]	Number[4]	Kind Code[5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation[6]
BL		JP	06-163599	A	06-10-1994	NEC Corp.	Abstract
BL		JP	06-84959	A	03-25-1994	Fujitsu Ltd.	Abstract
BL		JP	2001-210819	A	08-03-2001	Hitachi Cable Ltd.	Abstract
BL		JP	06-21106	A	01-28-1994	Hitachi Cable Ltd.	Abstract
BL		JP	2708863	B2	10-17-1997	Sanyo Electric Co., Ltd.	Abstract

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation[6]
BL		Feng Zhao et al., "Hall and photoluminescence studies of effects of the thickness of an additional $In_{0.3}Ga_{0.85}As/Al_{0.25}Ga_{0.75}As/GaAs$ high electron mobility transistors", *Materials Science in Semiconductor Processing*, Vol. 5, 2000, pp. 23-26	
BL		U. Strauss et al., "Carrier mobilities in graded $In_xGa_{1-x}As/Al_{0.2}Ga_{0.8}As$ quantum wells for high electron mobility transistors", *J. Appl. Phys.*, Vol. 80, No. 1, July 1, 1996, pp. 322-325	
BL		J.W. Matthews et al., "Defects in Epitaxial Multilayers", *Journal of Crystal Growth*, Vol. 27, 1974, pp. 118-125	
BL		J.W. Matthews et al., "Defects in Epitaxial Multilayers", *Journal of Crystal Growth*, Vol. 32, 1976, pp. 265-273	

Examiner Signature		Date Considered	2/14/2006

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1]Applicant's unique citation designation number (optional). [2]See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or in the comment box of this document. [3] Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). [4]For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5]Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6] Applicant is to indicate here if English language Translation is attached.